

General Purpose PPN Epitaxial Planar Transistor

BC857N3

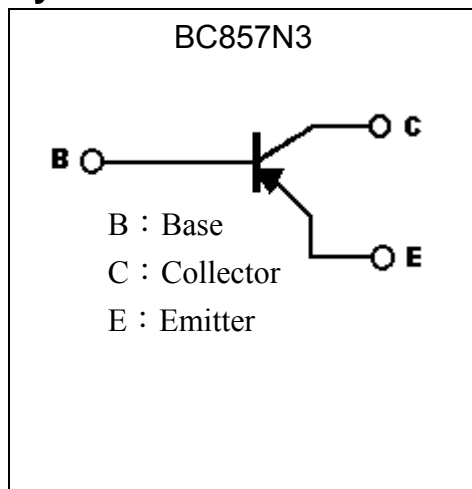
Description

- The BC857N3 is designed for general purpose switching and amplification applications.
- Complementary to BC847N3.
- Pb-free lead plating and halogen-free package

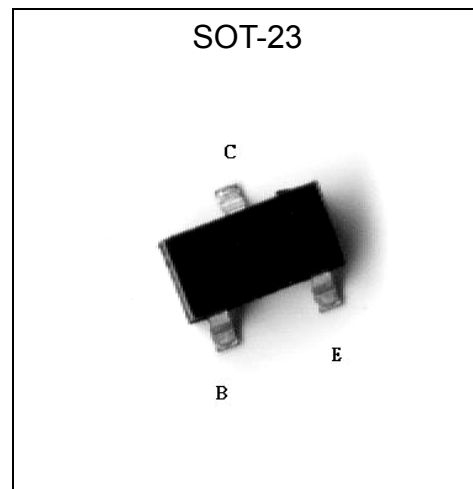
Features

- Low current, $I_{C(max)}=-200mA$
- Low voltage, $BV_{CEO}=-50V$.

Symbol

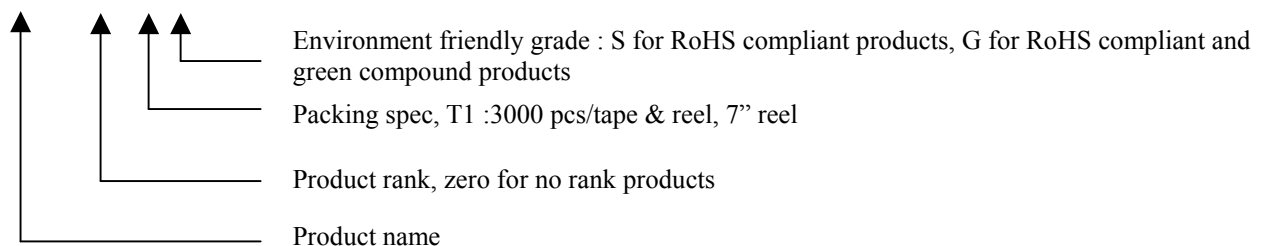


Outline



Ordering Information

Device	Package	Shipping
BC857N3-0-T1-G	SOT-23 (Pb-free lead plating and halogen-free package)	3000 pcs / Tape & Reel





Absolute Maximum Ratings (Ta=25°C)

Parameter	Symbol	Limits	Unit
Collector-Base Voltage	V _{CB0}	-50	V
Collector-Emitter Voltage	V _{CEO}	-50	V
Emitter-Base Voltage	V _{EBO}	-6	V
Collector Current (DC)	I _C	-200	mA
Collector Current (Pulse)	I _{CP}	-500	mA
Base Current (Pulse)	I _{BP}	-200	mA
Power Dissipation	P _D	250	mW
Operating Junction Temperature Range	T _j	-55~+150	°C
Storage Temperature Range	T _{stg}	-55~+150	°C

Thermal Data

Parameter	Symbol	Value	Unit
Thermal Resistance, Junction-to-ambient, max	R _{θJA}	500	°C/W

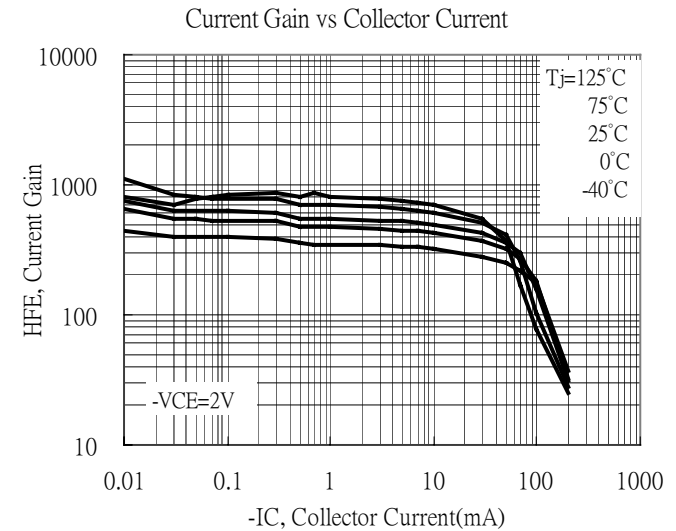
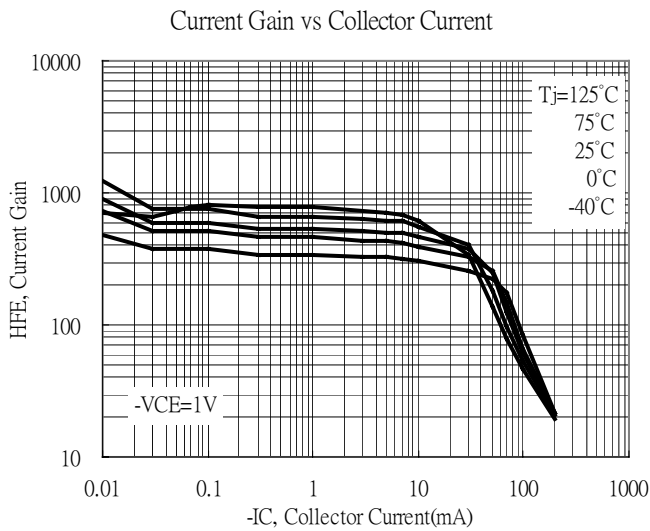
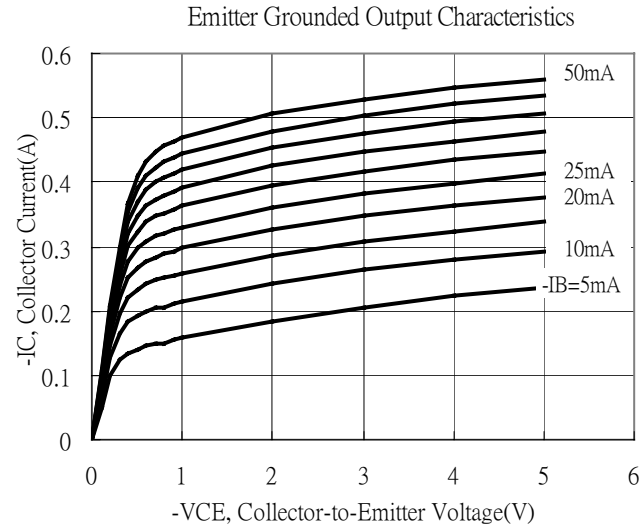
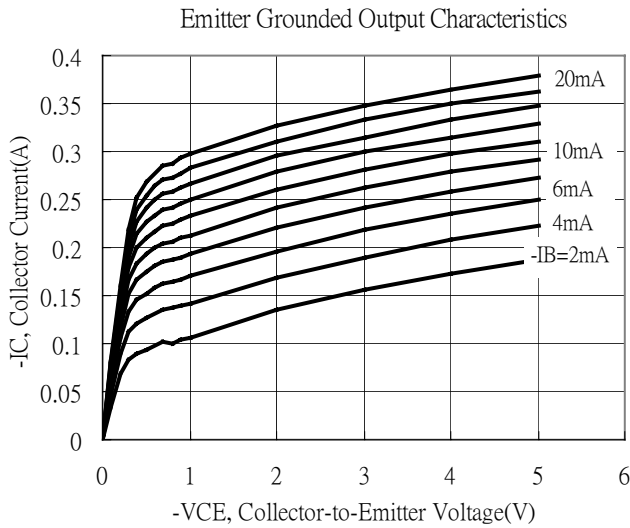
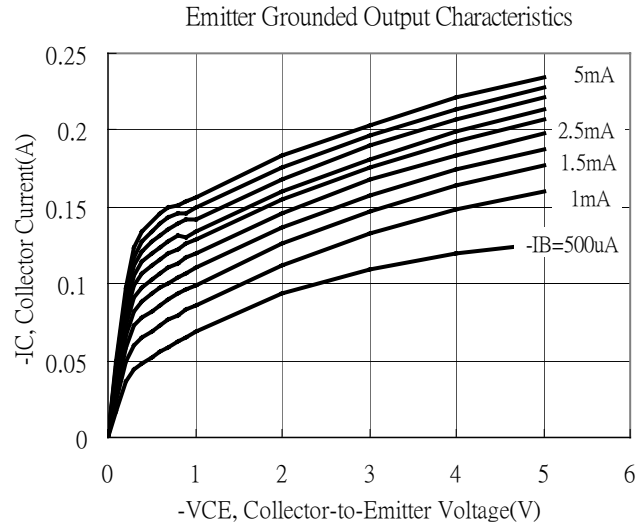
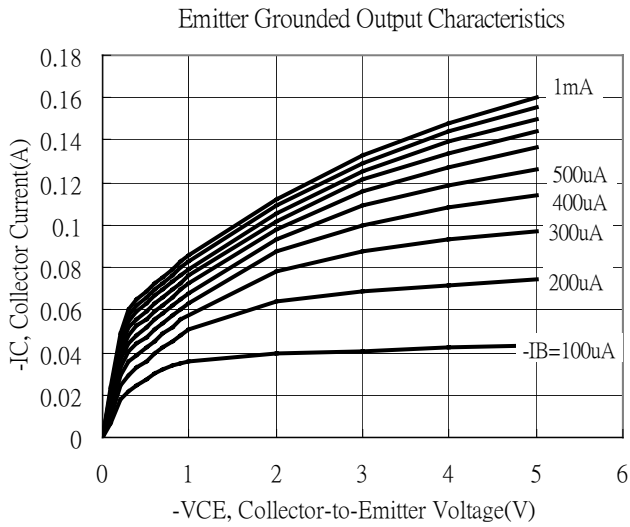
Characteristics (Ta=25°C)

Symbol	Min.	Typ.	Max.	Unit	Test Conditions
BV _{CB0}	-50	-	-	V	I _C =-100μA
BV _{CEO}	-50	-	-	V	I _C =-1mA
BV _{EBO}	-6	-	-	V	I _E =-10μA
I _{CB0}	-	-	-15	nA	V _{CB} =-30V
I _{EBO}	-	-	-100	nA	V _{EB} =-6V
*V _{CE(sat)} 1	-	-72	-200	mV	I _C =-10mA, I _B =-0.5mA
*V _{CE(sat)} 2	-	-220	-400	mV	I _C =-100mA, I _B =-5mA
*V _{BE(sat)} 1	-	-700	-	mV	I _C =-10mA, I _B =-0.5mA
*V _{BE(sat)} 2	-	-830	-	mV	I _C =-100mA, I _B =-5mA
*V _{BE(on)} 1	-600	-640	-750	mV	V _{CE} =-5V, I _C =-2mA
*V _{BE(on)} 2	-	-	-770	mV	V _{CE} =-5V, I _C =-10mA
*h _{FE}	420	-	800	-	V _{CE} =-5V, I _C =-2mA
f _T	100	-	-	MHz	V _{CE} =-5V, I _E =-10mA, f=100MHz
Cob	-	3.7	-	pF	V _{CB} =-10V, I _E =0A, f=1MHz

*Pulse Test: Pulse Width ≤380μs, Duty Cycle≤2%



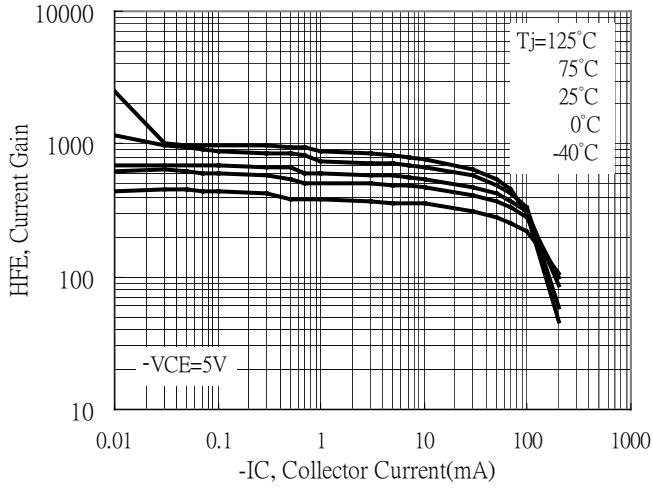
Typical Characteristics



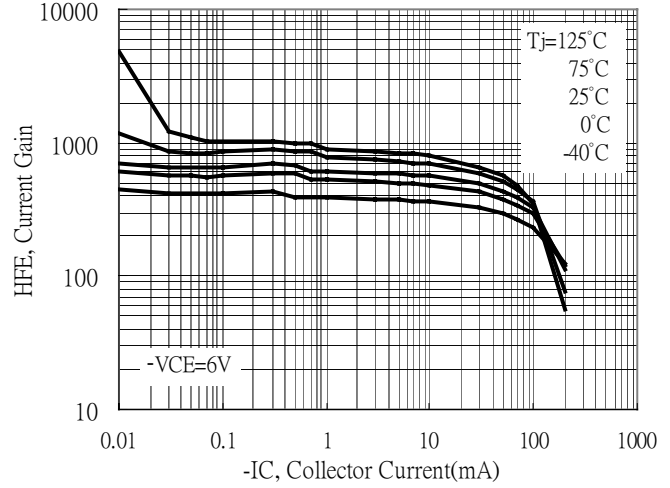


Typical Characteristics(Cont.)

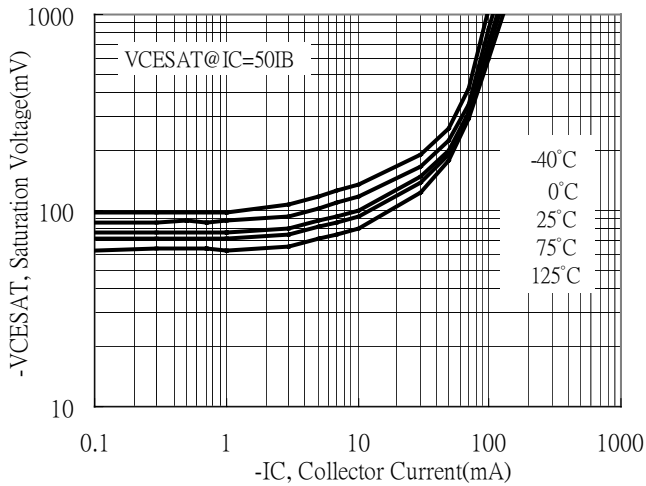
Current Gain vs Collector Current



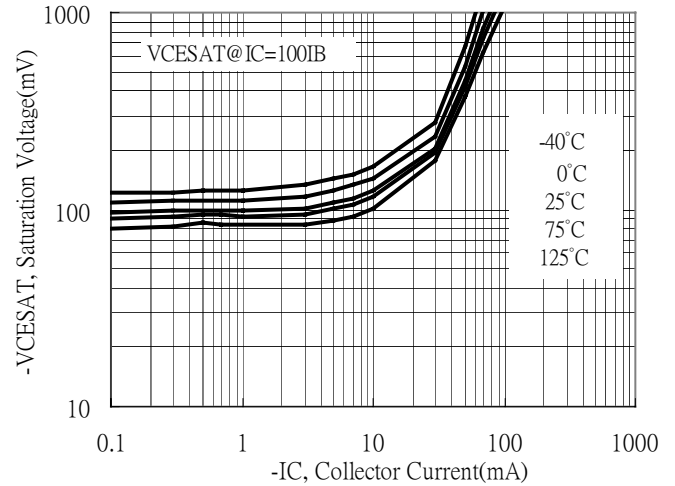
Current Gain vs Collector Current



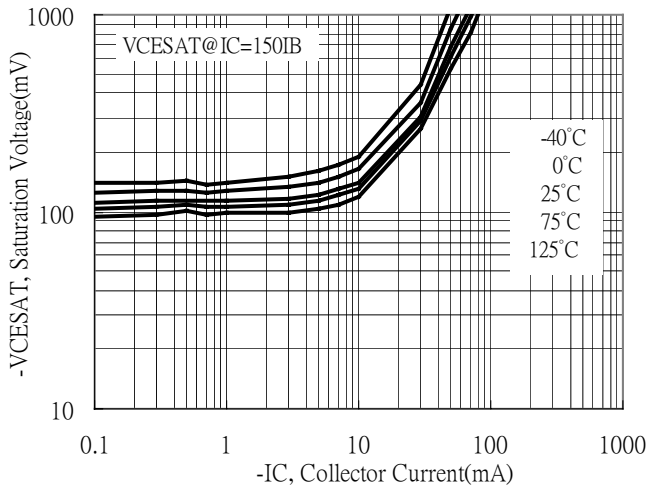
Saturation Voltage vs Collector Current



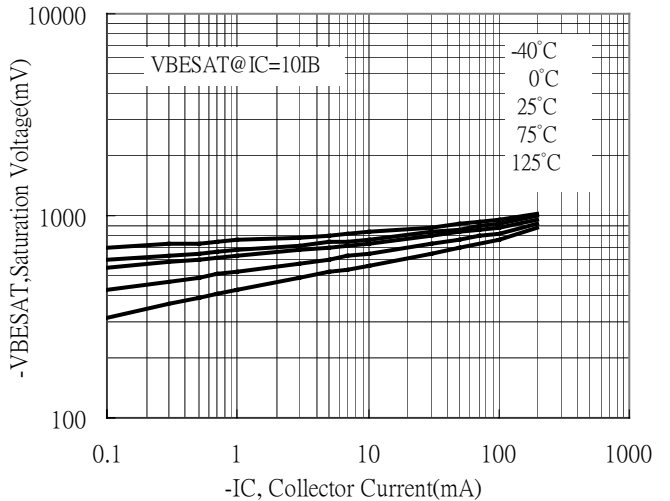
Saturation Voltage vs Collector Current



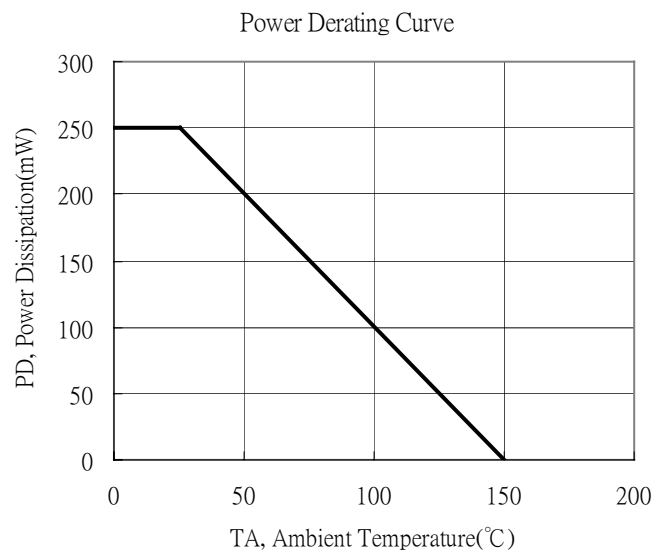
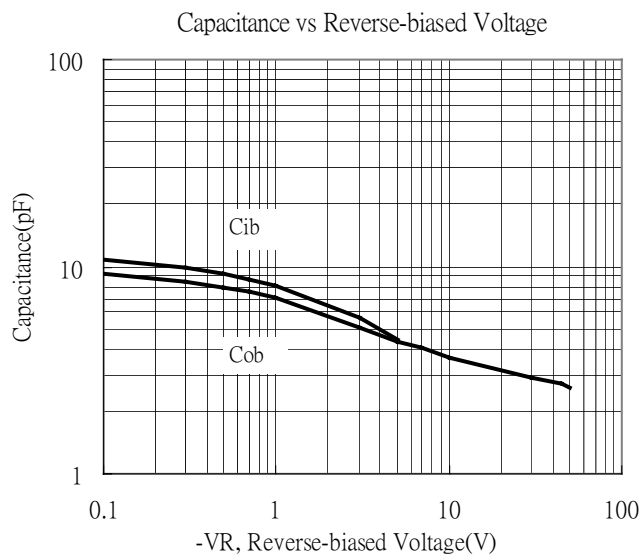
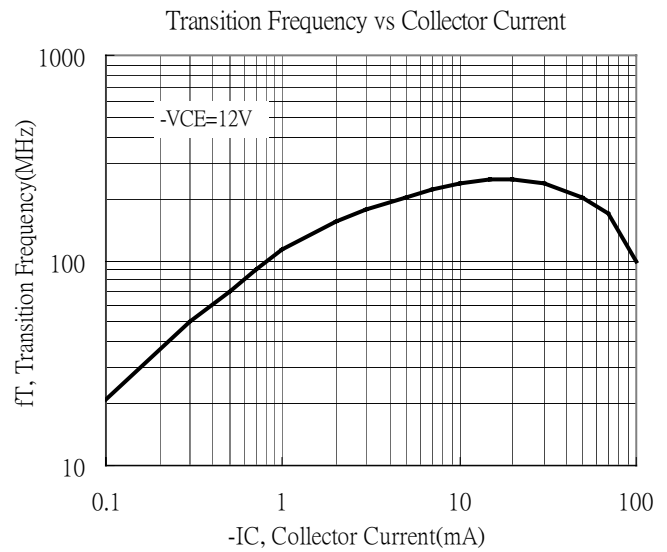
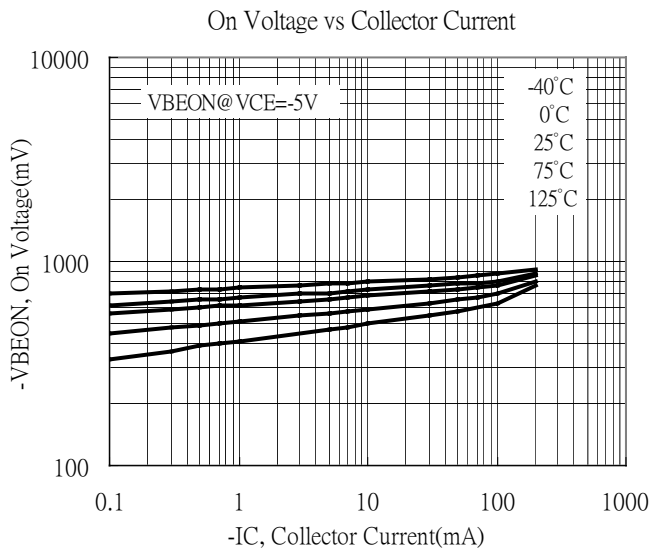
Saturation Voltage vs Collector Current



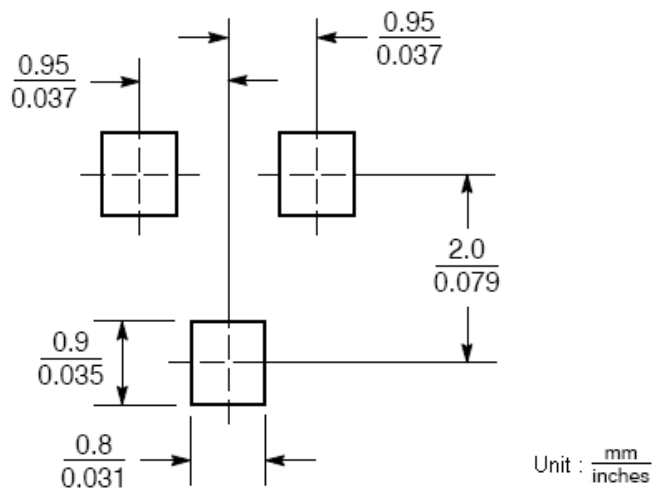
Saturation Voltage vs Collector Current



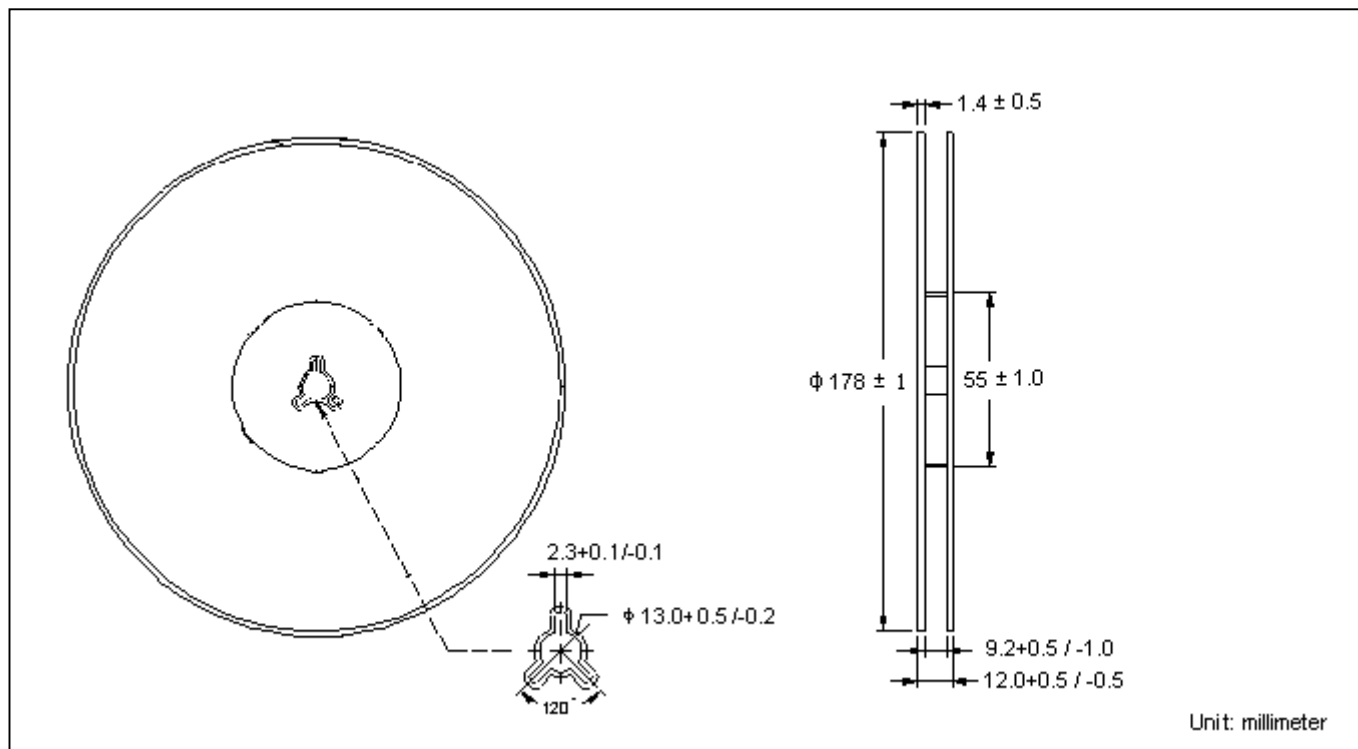
Typical Characteristics(Cont.)



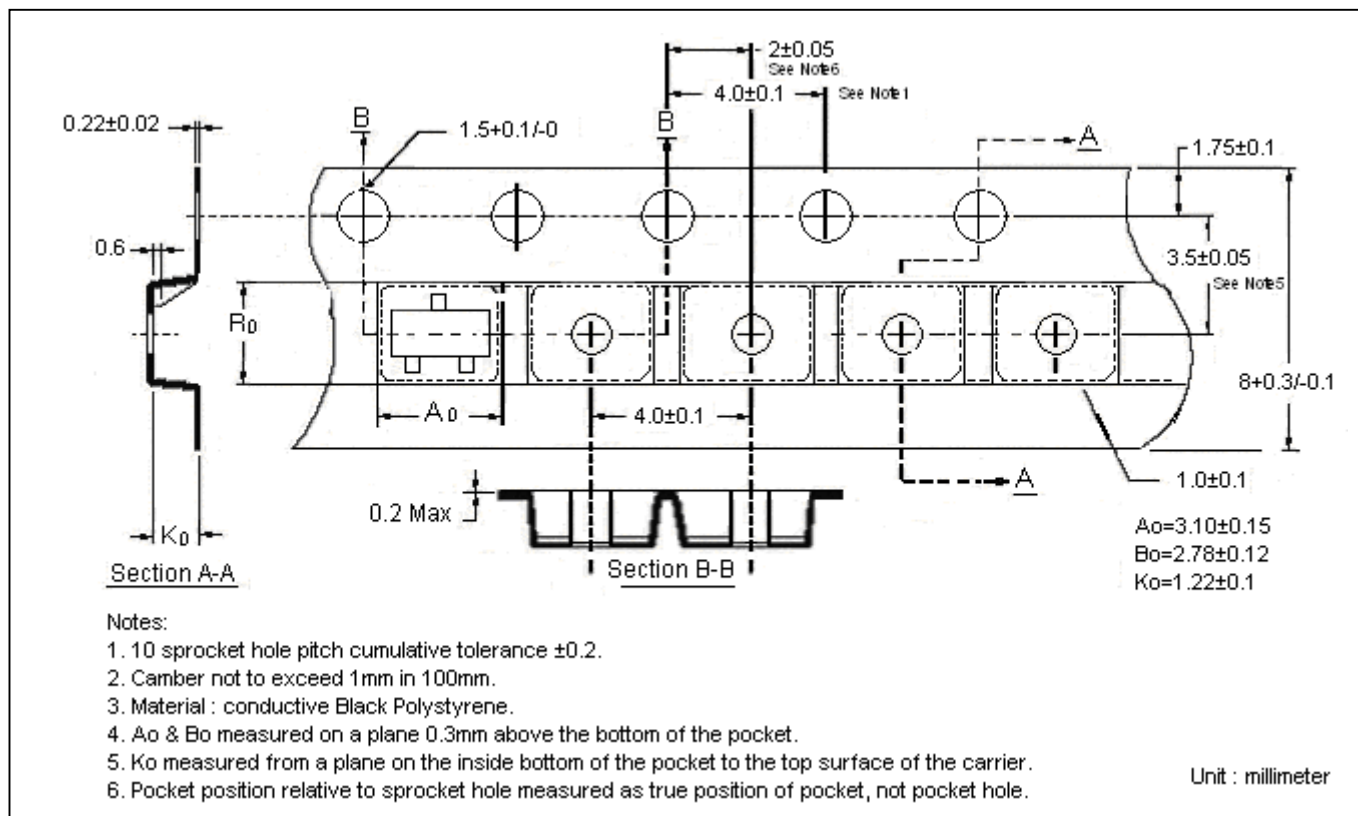
Recommended Soldering Footprint



Reel Dimension



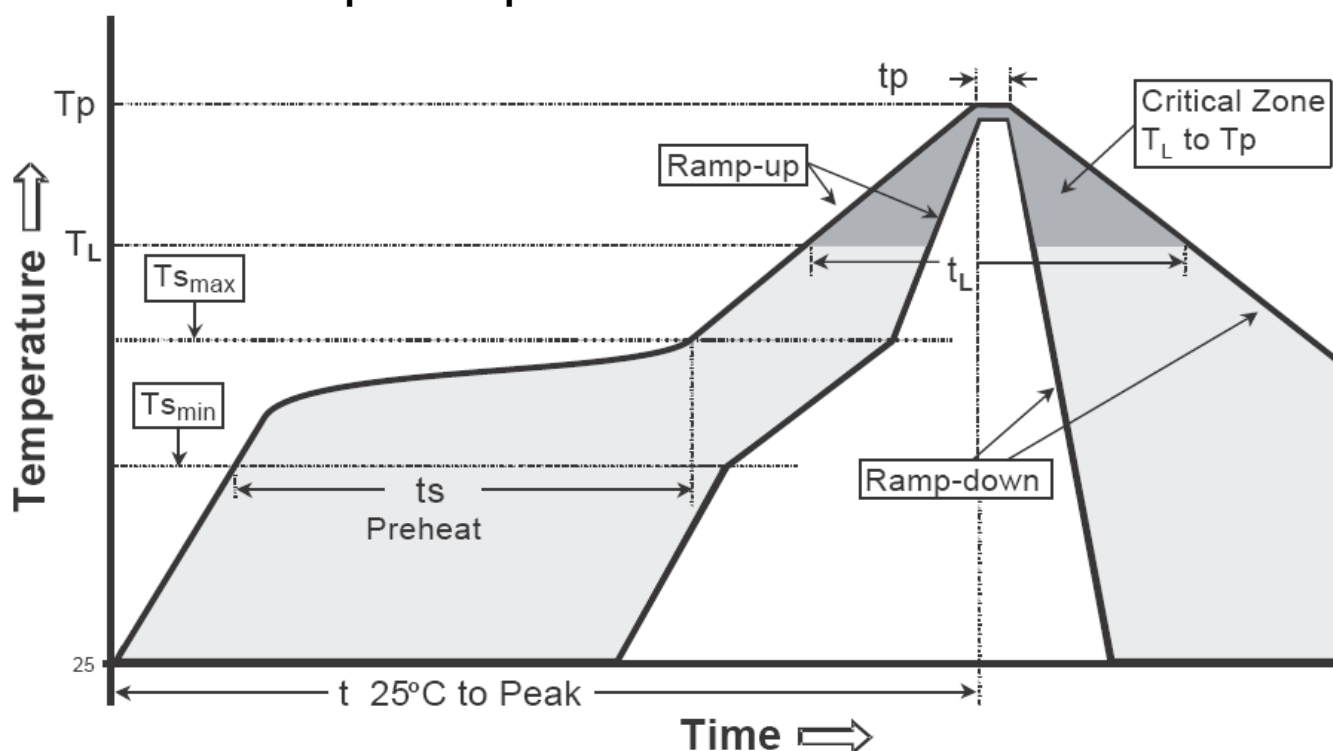
Carrier Tape Dimension



Recommended wave soldering condition

Product	Peak Temperature	Soldering Time
Pb-free devices	260 +0/-5 °C	5 +1/-1 seconds

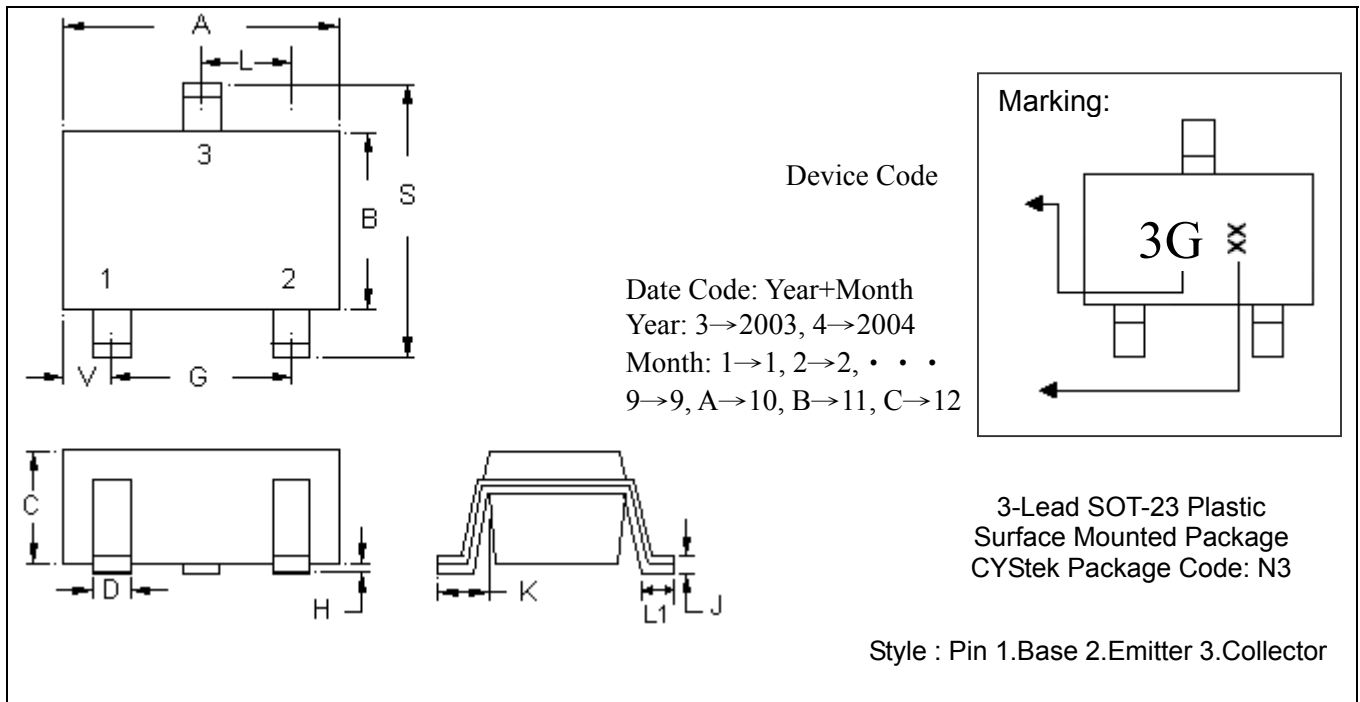
Recommended temperature profile for IR reflow



Profile feature	Sn-Pb eutectic Assembly	Pb-free Assembly
Average ramp-up rate (Tsmax to Tp)	3°C/second max.	3°C/second max.
Preheat		
-Temperature Min(Ts min)	100°C	150°C
-Temperature Max(Ts max)	150°C	200°C
-Time(ts min to ts max)	60-120 seconds	60-180 seconds
Time maintained above:		
-Temperature (Tl)	183°C	217°C
- Time (tL)	60-150 seconds	60-150 seconds
Peak Temperature(Tp)	240 +0/-5 °C	260 +0/-5 °C
Time within 5°C of actual peak temperature(tp)	10-30 seconds	20-40 seconds
Ramp down rate	6°C/second max.	6°C/second max.
Time 25 °C to peak temperature	6 minutes max.	8 minutes max.

Note : All temperatures refer to topside of the package, measured on the package body surface.

SOT-23 Dimension



*:Typical

DIM	Inches		Millimeters		DIM	Inches		Millimeters	
	Min.	Max.	Min.	Max.		Min.	Max.	Min.	Max.
A	0.1102	0.1204	2.80	3.04	J	0.0032	0.0079	0.08	0.20
B	0.0472	0.0669	1.20	1.70	K	0.0118	0.0266	0.30	0.67
C	0.0335	0.0512	0.89	1.30	L	0.0335	0.0453	0.85	1.15
D	0.0118	0.0197	0.30	0.50	S	0.0830	0.1161	2.10	2.95
G	0.0669	0.0910	1.70	2.30	V	0.0098	0.0256	0.25	0.65
H	0.0000	0.0040	0.00	0.10	L1	0.0118	0.0197	0.30	0.50

- Notes :
- Controlling dimension : millimeters.
 - Maximum lead thickness includes lead finish thickness, and minimum lead thickness is the minimum thickness of base material.
 - If there is any question with packing specification or packing method, please contact your local CYStek sales office.

Material :

- Lead :Pure tin plated.
- Mold Compound : Epoxy resin family, flammability solid burning class:UL94V-0.

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